



- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ ESD Protection
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench

Product Summary

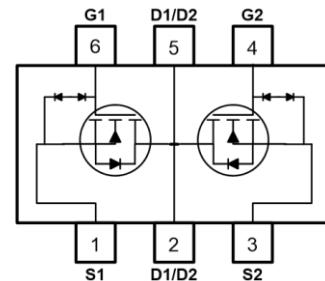
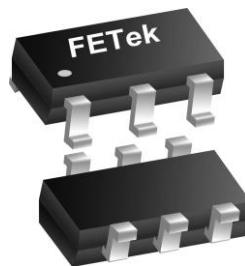
BVDSS	RDS(on)	ID
20V	23.5mΩ	5.5A

Description

The FKQ2721 is the low RDSON trenched N-CH MOSFETs with robust ESD protection. This product is suitable for Lithium-ion battery pack applications.

The FKQ2721 meet the RoHS and Green Product requirement with full function reliability approved.

TSOP6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D @T _A =25°C	Continuous Drain Current ¹	5.5	A
I _D @T _A =70°C	Continuous Drain Current ¹	4.4	A
I _{DM}	Pulsed Drain Current ²	22	A
P _D @T _A =25°C	Total Power Dissipation ³	1.25	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ¹	---	100	°C/W

N-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

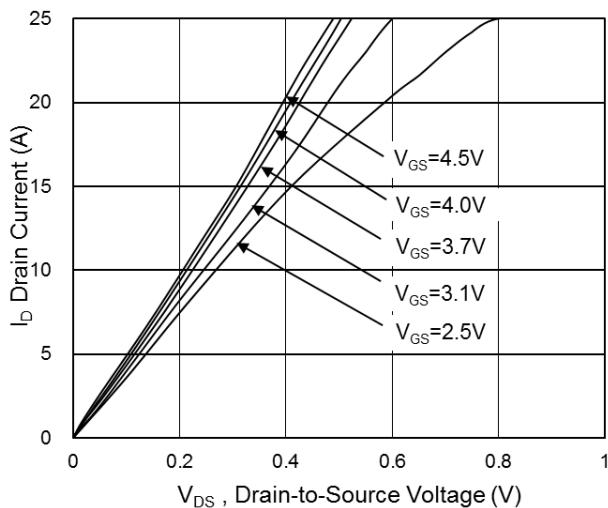
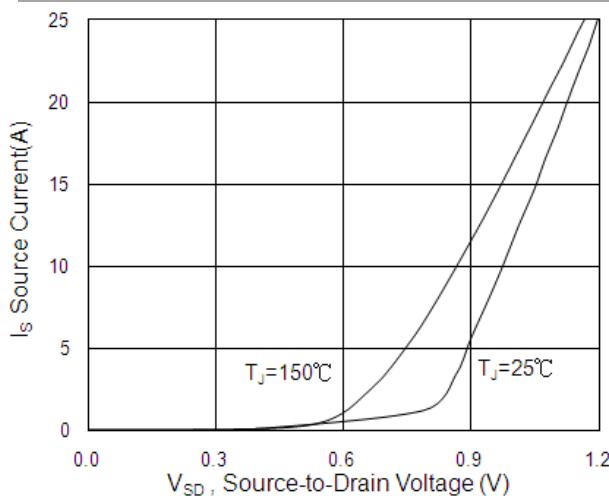
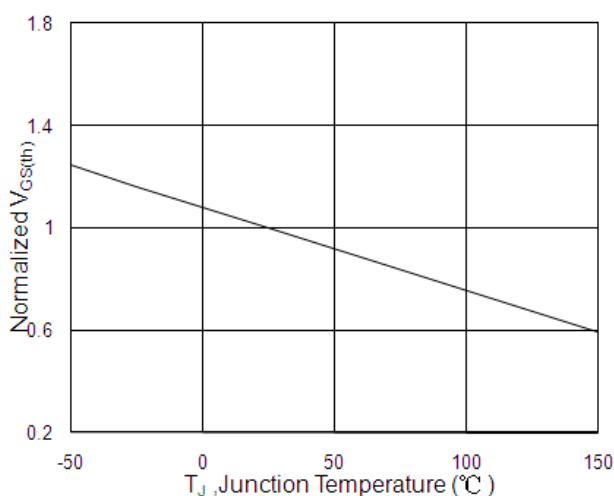
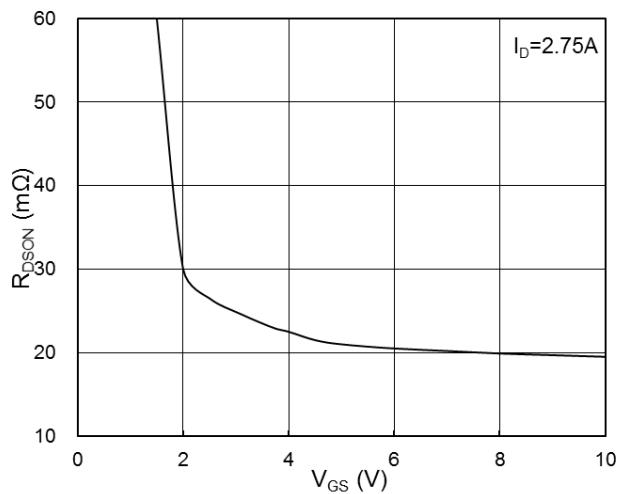
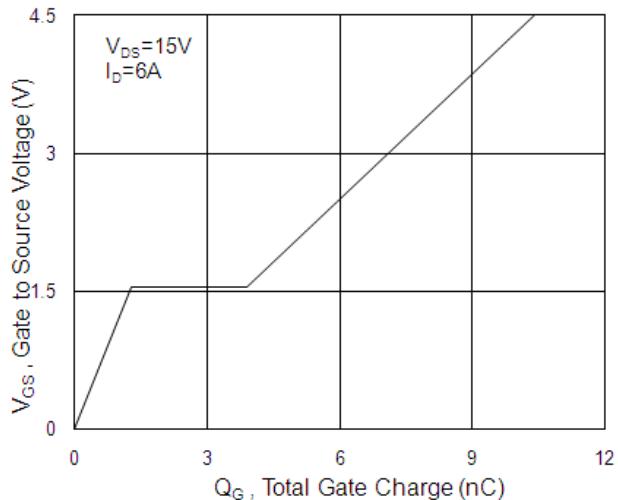
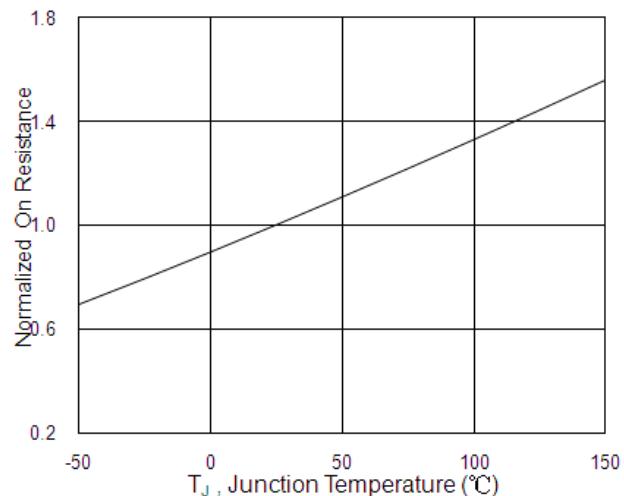
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	20	---	---	V
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=4.5\text{V}$, $I_D=2.75\text{A}$	17.5	20.5	23.5	$\text{m}\Omega$
		$V_{\text{GS}}=4.0\text{V}$, $I_D=2.75\text{A}$	18.5	21.5	24.5	
		$V_{\text{GS}}=3.7\text{V}$, $I_D=2.75\text{A}$	19.0	22.5	26.5	
		$V_{\text{GS}}=3.1\text{V}$, $I_D=2.75\text{A}$	19.5	24.5	29.5	
		$V_{\text{GS}}=2.5\text{V}$, $I_D=2.75\text{A}$	21.5	28.5	35.5	
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}$, $I_D=250\mu\text{A}$	0.5	0.7	1.2	V
I_{DSs}	Drain-Source Leakage Current	$V_{\text{DS}}=16\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=25^\circ\text{C}$	---	---	1	uA
		$V_{\text{DS}}=16\text{V}$, $V_{\text{GS}}=0\text{V}$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 8\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 10	uA
g_{fs}	Forward Transconductance	$V_{\text{DS}}=5\text{V}$, $I_D=3\text{A}$	---	18	---	S
Q_g	Total Gate Charge	$V_{\text{DS}}=15\text{V}$, $V_{\text{GS}}=4.5\text{V}$, $I_D=6\text{A}$	---	10.4	---	nC
Q_{gs}	Gate-Source Charge		---	1.6	---	
Q_{gd}	Gate-Drain Charge		---	2.9	---	
$T_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}}=10\text{V}$, $V_{\text{GS}}=4.5\text{V}$, $R_G=3.3\Omega$	---	3.4	---	ns
T_r	Rise Time		---	11.0	---	
$T_{\text{d(off)}}$	Turn-Off Delay Time		---	35	---	
T_f	Fall Time		---	4.2	---	
C_{iss}	Input Capacitance	$V_{\text{DS}}=15\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	635	---	pF
C_{oss}	Output Capacitance		---	67	---	
C_{rss}	Reverse Transfer Capacitance		---	61	---	

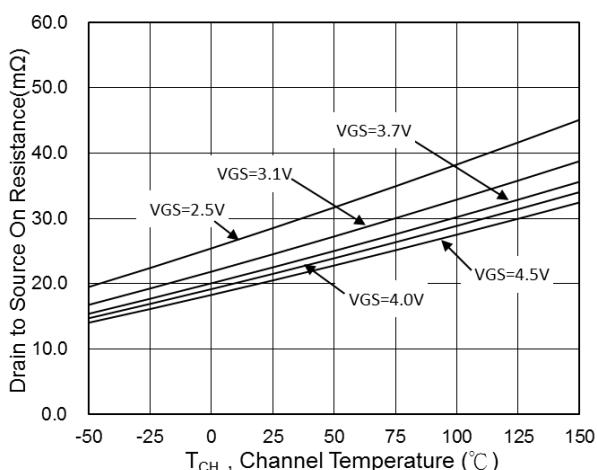
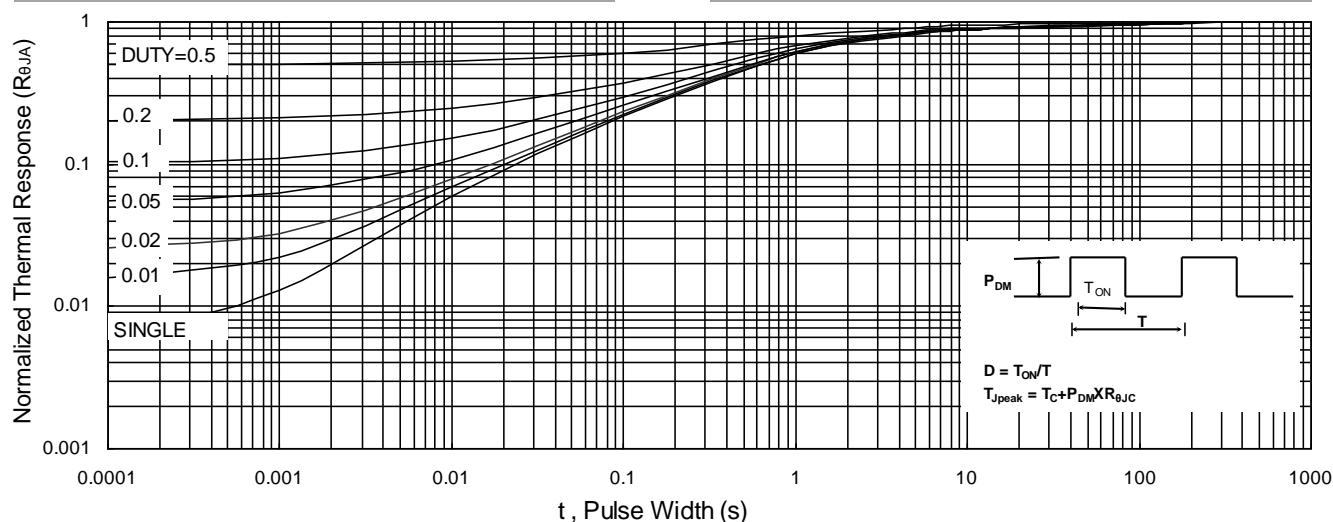
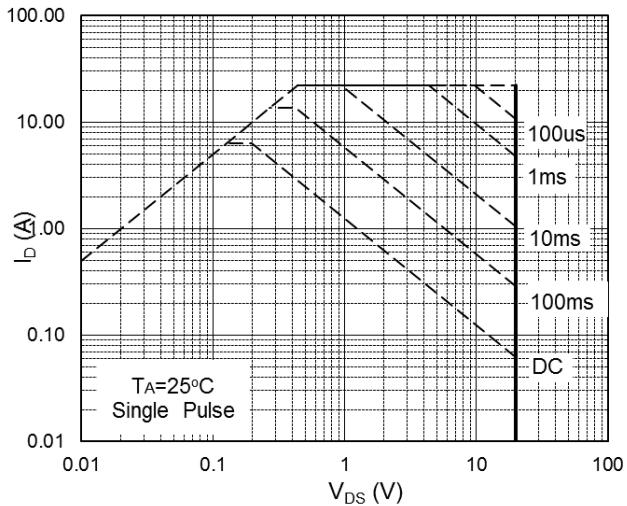
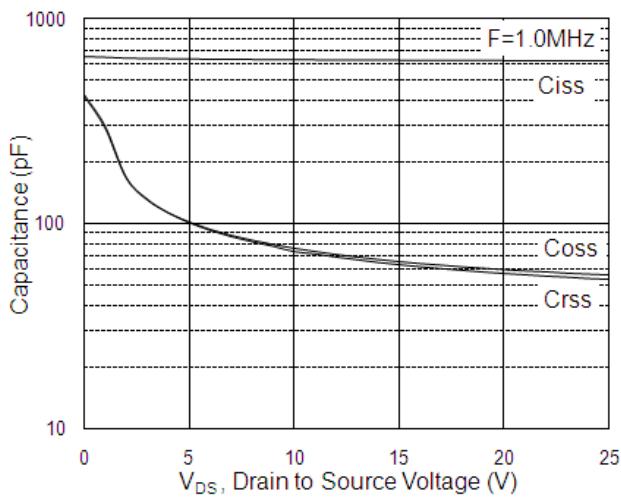
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_s	Continuous Source Current ^{1,4}	$V_G=V_D=0\text{V}$, Force Current	---	---	5.5	A
V_{SD}	Diode Forward Voltage ²	$V_{\text{GS}}=0\text{V}$, $I_s=1\text{A}$, $T_J=25^\circ\text{C}$	---	0.75	1.2	V

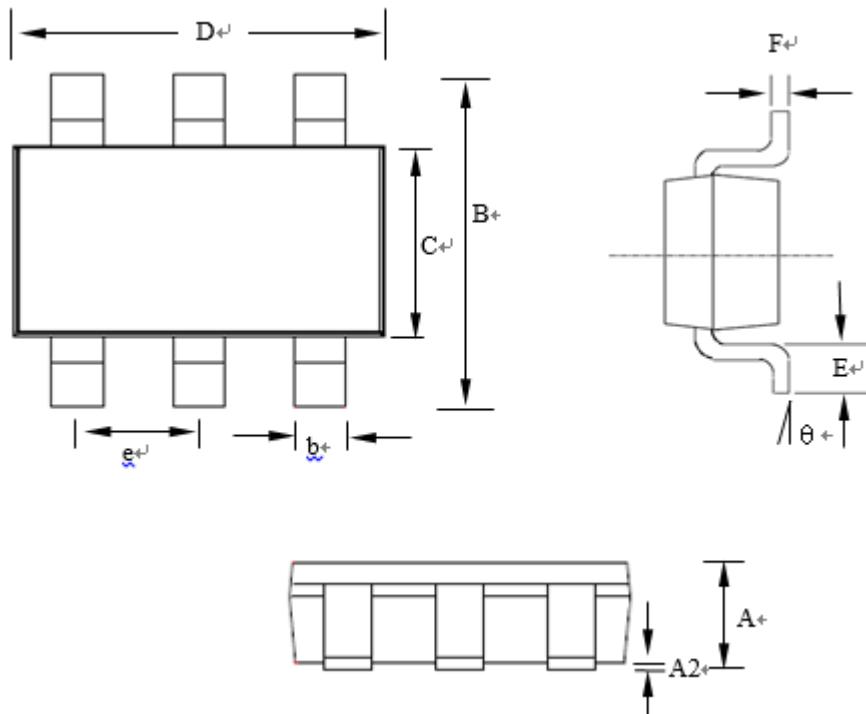
Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, $t \leq 10\text{s}$.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

N-Channel Typical Characteristics

Fig.1 Typical Output Characteristics

Fig.3 Forward Characteristics of Reverse

Fig.5 Normalized $V_{GS(th)}$ vs. T_J

Fig.2 On-Resistance vs. G-S voltage

Fig.4 Gate-Charge Characteristics

Fig.6 Normalized $R_{DS(on)}$ vs. T_J

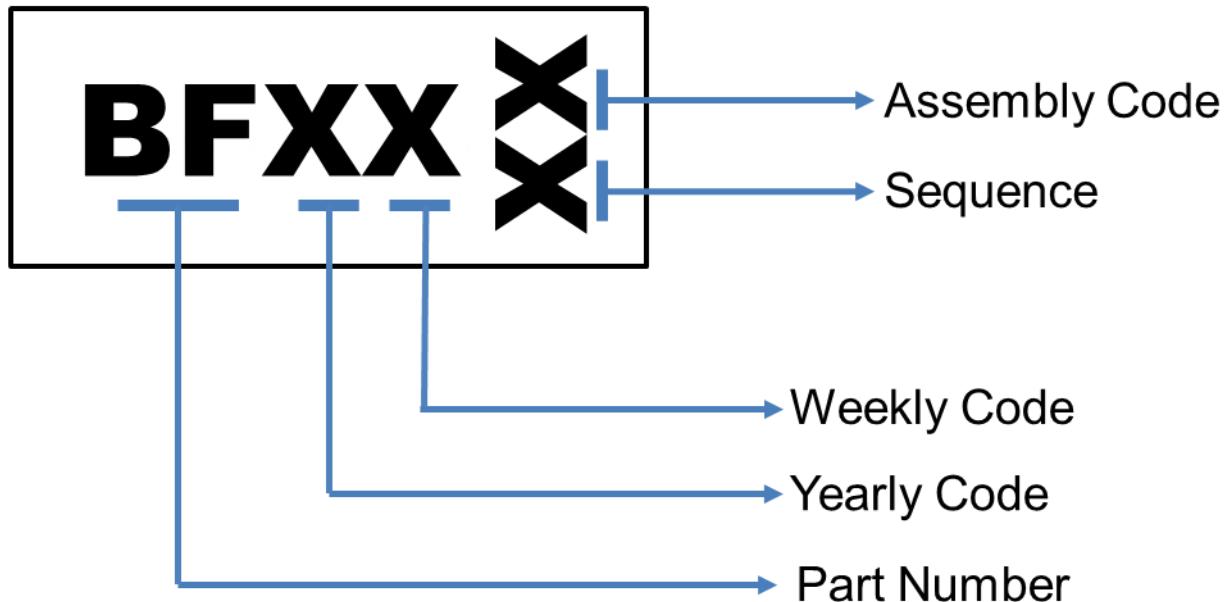


TSOP6 Package Outline Dimensions



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	--	0.9	0.028	--	0.035
A2	0.00	--	0.10	0.000	--	0.004
B	2.60	2.80	3.00	0.102	0.110	0.118
C	1.40	1.60	1.80	0.055	0.063	0.071
D	2.70	2.90	3.10	0.106	0.114	0.122
E	0.30	0.40	0.60	0.012	0.016	0.024
F	0.07	0.127	0.20	0.003	0.005	0.008
b	0.30	0.40	0.50	0.012	0.016	0.020
e	--	0.95	--	--	0.037	--
theta	0°	5°	10°	0°	5°	10°

Marking Instruction



TSOP6 Tape and Reel Data

